

**ABSTRACT**

[0043] Disclosed herein is a method for forming a bit line of a flash device capable of reducing loss of an interlayer insulation film between the bit line patterns. The method includes forming a bit line metal hard-mask pattern prior to forming a bit line mask pattern, preventing an interval between the bit lines from being reduced by controlling conditions of a cleaning process prior to forming a metal film. The method obviates an additional process of removing the metal hard-mask film since the metal hard-mask film is also removed at the same time of carrying out a bit line planarization process.